

ABSTRACT OF THE DISCLOSURE

In order to improve the characteristic of the PZT film (insulation film of capacitor) of the PZT capacitor, after forming the amorphous PZT film, the amorphous PZT film is crystallized from at least the upper surface of the amorphous PZT film to form the PZT crystal film by employing the process whose sequence is reverse to that of the conventional process. In this case, the amorphous PZT film, which contains excessive oxygen and formed on the upper surface of the amorphous PZT film, is used as a seed.

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